

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims, including those in the First Preliminary Amendment, in the application:

Listing of Claims:

Claim 1 (canceled).

Claim 2 (currently amended): A sputtering target ~~having~~ comprising:
a target structure where the having an average crystallite size ~~is~~ of 1nm to 5nm;
said sputtering target being made of an alloy having a three or more
component system containing at least one element selected from the
group consisting of Zr, Pt, Pd, Fe, Co, and Cu as its primary
component in an atomic ratio of 50at% or more, said alloy possessing
the requirements of a metallic glass satisfying an atomic radius
difference of 12% or more and negative heat of mixing; and
said sputtering target having a relative density of at least 96.4% and being an
amorphous material obtained by sintering gas atomized powder.

Claim 3 (currently amended): A sputtering target ~~having a structure where the~~
according to claim 2, wherein said average crystallite size of said target structure is 1nm to
2nm.

Claims 4-13 (canceled).

Claim 14 (new): A sputtering target according to claim 3, wherein said primary component of said alloy is Zr, and wherein said alloy contains at least one element selected from a group consisting of Cu, Ni and Al.

Claim 15 (new): A sputtering target according to claim 3, wherein said primary component of said alloy is Pt, and wherein said alloy contains at least one element selected from a group consisting of Pd, Cu and P.

Claim 16 (new): A sputtering target according to claim 3, wherein said primary component of said alloy is Pd, and wherein said alloy contains at least one element selected from a group consisting of Cu, Ni and P.

Claim 17 (new): A sputtering target according to claim 3, wherein said primary component of said alloy is Fe, and wherein said alloy contains B and at least one element selected from a group consisting of Ti, V, Cr, Zr, Nb, Mo, Hf, Ta and W.

Claim 18 (new): A sputtering target according to claim 3, wherein said primary component of said alloy is Co, and wherein said alloy contains at least one element selected from a group consisting of Fe, Ta and B.

Claim 19 (new): A sputtering target according to claim 3, wherein said primary component of said alloy is Cu, and wherein said alloy contains at least one element selected from a group consisting of Zr and Ti.

Claim 20 (new): A sputtering target according to claim 2, wherein said primary component of said alloy is Zr, and wherein said alloy contains at least one element selected from a group consisting of Cu, Ni and Al.

Claim 21 (new): A sputtering target according to claim 2, wherein said primary component of said alloy is Pt, and wherein said alloy contains at least one element selected from a group consisting of Pd, Cu and P.

Claim 22 (new): A sputtering target according to claim 2, wherein said primary component of said alloy is Pd, and wherein said alloy contains at least one element selected from a group consisting of Cu, Ni and P.

Claim 23 (new): A sputtering target according to claim 2, wherein said primary component of said alloy is Fe, and wherein said alloy contains B and at least one element selected from a group consisting of Ti, V, Cr, Zr, Nb, Mo, Hf, Ta and W.

Claim 24 (new): A sputtering target according to claim 2, wherein said primary component of said alloy is Co, and wherein said alloy contains at least one element selected from a group consisting of Fe, Ta and B.

Claim 25 (new): A sputtering target according to claim 2, wherein said primary component of said alloy is Cu, and wherein said alloy contains at least one element selected from a group consisting of Zr and Ti.

Claim 26 (new): A method of manufacturing a sputtering target, comprising the step of sintering a gas atomized powder to produce a sputtering target having an amorphous structure with an average crystallite size of 1nm to 5nm and a relative density of at least 96.4% , said powder being an alloy powder having a three or more component system containing at least one element selected from the group consisting of Zr, Pt, Pd, Fe, Co, and Cu as its primary component in an atomic ratio of 50at% or more, and said alloy possessing the requirements of a metallic glass satisfying an atomic radius difference of 12% or more and negative heat of mixing.

Claim 27 (new): A method according to claim 26, wherein said average crystallite size of said target structure produced by said method is 1nm to 2nm.

Claim 28 (new): A method according to claim 26, wherein said primary component of said alloy is Zr, and wherein said alloy contains at least one element selected from a group consisting of Cu, Ni and Al.

Claim 29 (new): A method according to claim 26, wherein said primary component of said alloy is Pt, and wherein said alloy contains at least one element selected from a group consisting of Pd, Cu and P.

Claim 30 (new): A method according to claim 26, wherein said primary component of said alloy is Pd, and wherein said alloy contains at least one element selected from a group consisting of Cu, Ni and P.

Claim 31 (new): A method according to claim 26, wherein said primary component of said alloy is Fe, and wherein said alloy contains B and at least one element selected from a group consisting of Ti, V, Cr, Zr, Nb, Mo, Hf, Ta and W.

Claim 32 (new): A method according to claim 26, wherein said primary component of said alloy is Co, and wherein said alloy contains at least one element selected from a group consisting of Fe, Ta and B.

Claim 33 (new): A method according to claim 26, wherein said primary component of said alloy is Cu, and wherein said alloy contains at least one element selected from a group consisting of Zr and Ti